

## N-Channel 8-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
8	0.086 at $V_{GS} = 4.5$ V	1.34 <sup>a</sup>	7.1
	0.093 at $V_{GS} = 2.5$ V	1.29	
	0.102 at $V_{GS} = 1.8$ V	1.23	
	0.120 at $V_{GS} = 1.5$ V	0.7	

### FEATURES

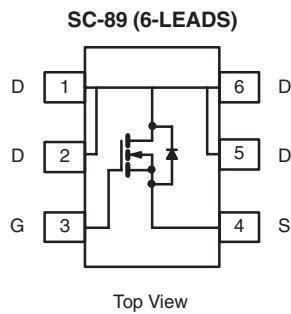
- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  Tested

### APPLICATIONS

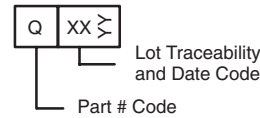
- Load Switch for Portable Devices



**RoHS**  
COMPLIANT



Marking Code



Ordering Information: Si1050X-T1-E3 (Lead (Pb)-free)  
Si1050X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	8	V
Gate-Source Voltage	$V_{GS}$	$\pm 5$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$T_A = 25$ °C	1.34 <sup>b, c</sup>	A
	$T_A = 70$ °C	1.07 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	6	
Continuous Source-Drain Diode Current	$I_S$	0.2 <sup>b, c</sup>	
Maximum Power Dissipation <sup>a</sup>	$T_A = 25$ °C	0.236 <sup>b, c</sup>	W
	$T_A = 70$ °C	0.151 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$t \leq 5$ s	$R_{thJA}$	440	530	°C/W
	Steady State		540	650	

Notes:

- Based on  $T_C = 25$  °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$  s.
- Maximum under steady state conditions is 650 °C/W.

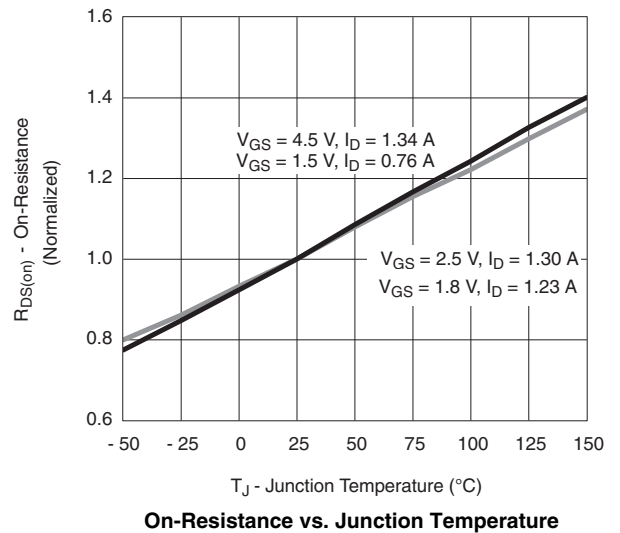
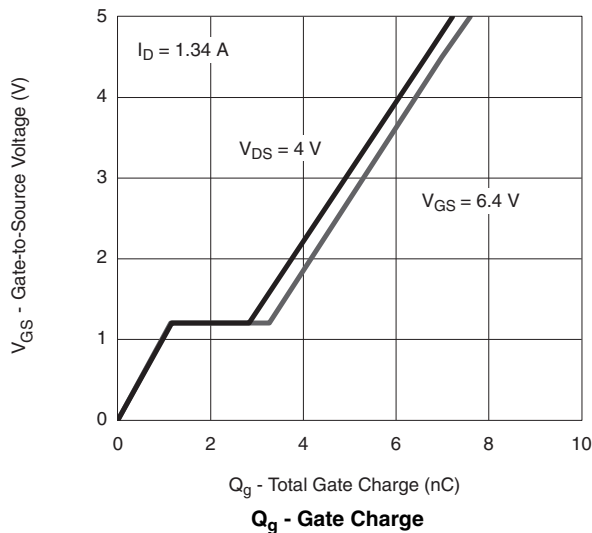
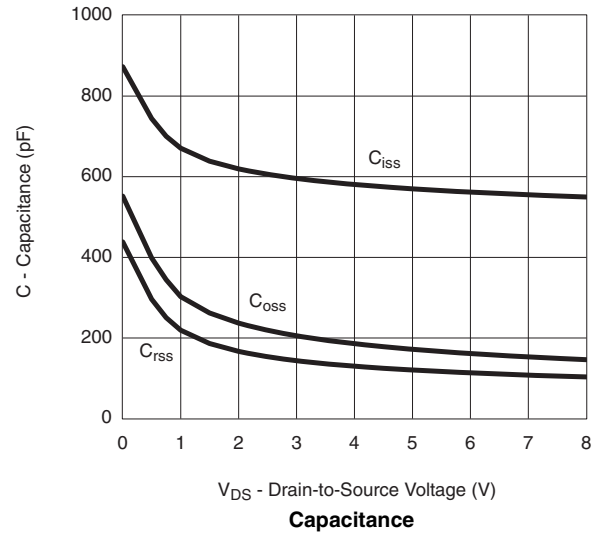
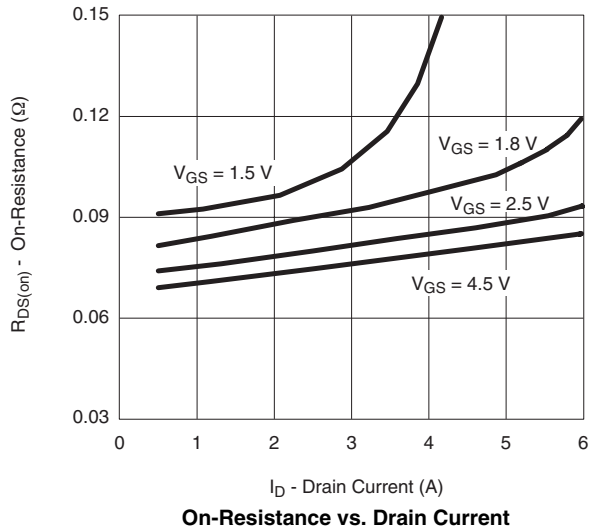
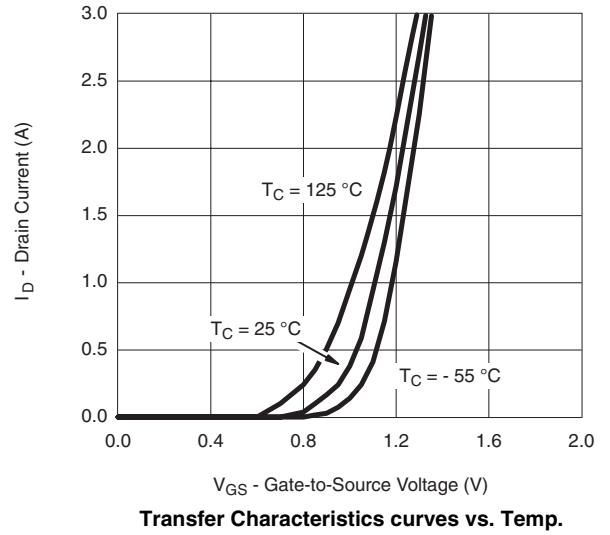
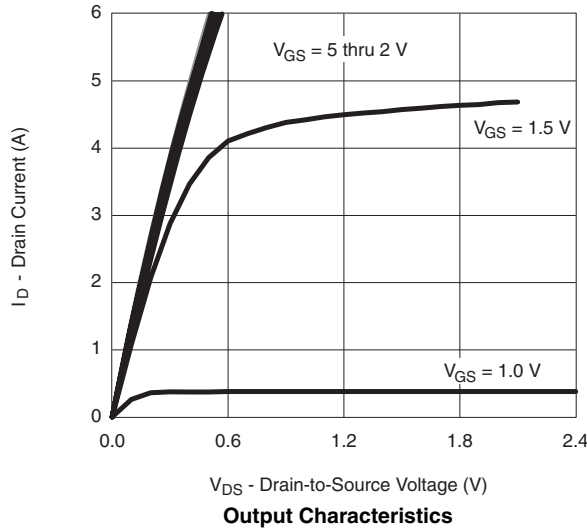
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	8			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		18.2		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-2.55		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.35		0.9	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}$			1	nA
		$V_{DS} = 8\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			10	$\mu\text{A}$
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	6			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 1.34\text{ A}$		0.071	0.086	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 1.29\text{ A}$		0.078	0.093	
		$V_{GS} = 1.8\text{ V}, I_D = 1.23\text{ A}$		0.085	0.102	
		$V_{GS} = 1.5\text{ V}, I_D = 0.76\text{ A}$		0.092	0.120	
Forward Transconductance	$g_{fs}$	$V_{DS} = 4\text{ V}, I_D = 1.34\text{ A}$		4.12		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		585		pF
Output Capacitance	$C_{oss}$			190		
Reverse Transfer Capacitance	$C_{rss}$			130		
Total Gate Charge	$Q_g$	$V_{DS} = 4\text{ V}, V_{GS} = 5\text{ V}, I_D = 1.34\text{ A}$		7.7	11.6	nC
				7.1	10.7	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 4\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1.34\text{ A}$		1.14		
Gate-Drain Charge	$Q_{gd}$			1.69		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		3.5	4.6	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 4\text{ V}, R_L = 3.6\text{ }\Omega$ $I_D \cong 1.1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		6.8	10.2	ns
Rise Time	$t_r$			35	53	
Turn-Off Delay Time	$t_{d(off)}$			25	37.5	
Fall Time	$t_f$			6	9	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				6	A
Body Diode Voltage	$V_{SD}$	$I_S = 1.0\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		18.5	28	nC
Body Diode Reverse Recovery Charge	$Q_{rr}$			3.7	5.7	ns
Reverse Recovery Fall Time	$t_a$			6.7		
Reverse Recovery Rise Time	$t_b$			11.8		

Notes:

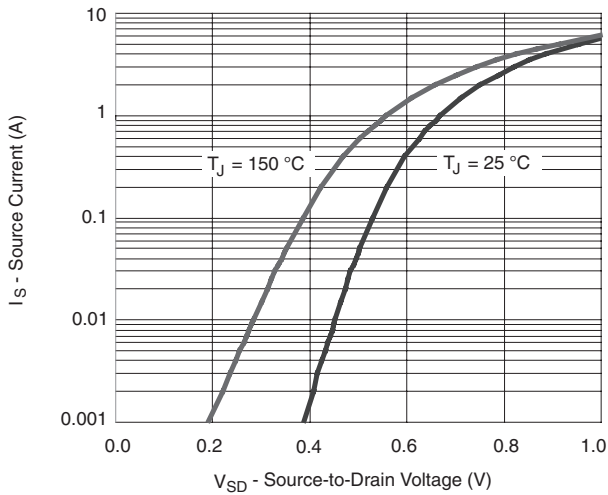
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

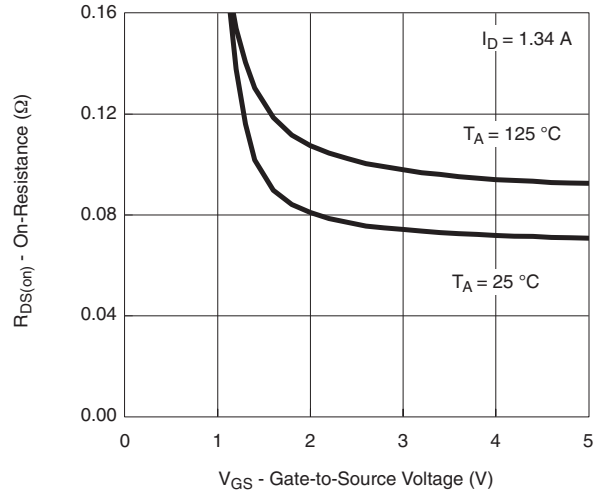
**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



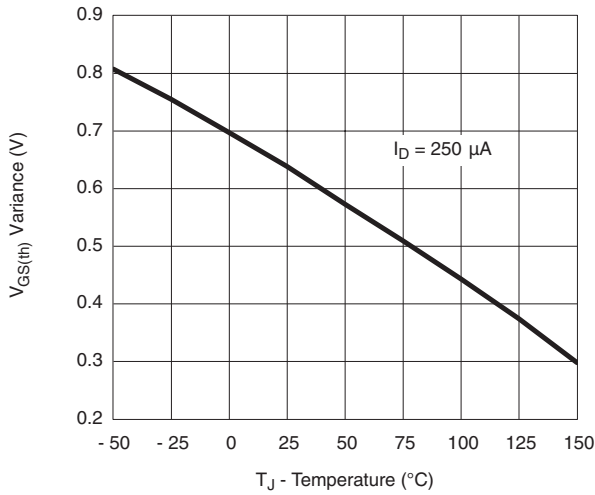
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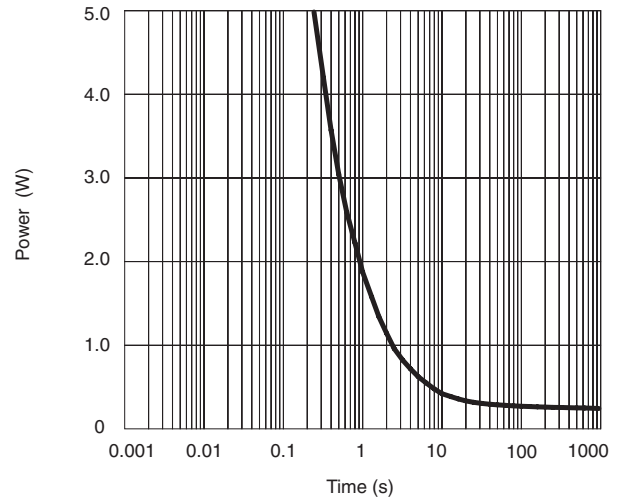
**Source-Drain Diode Forward Voltage**



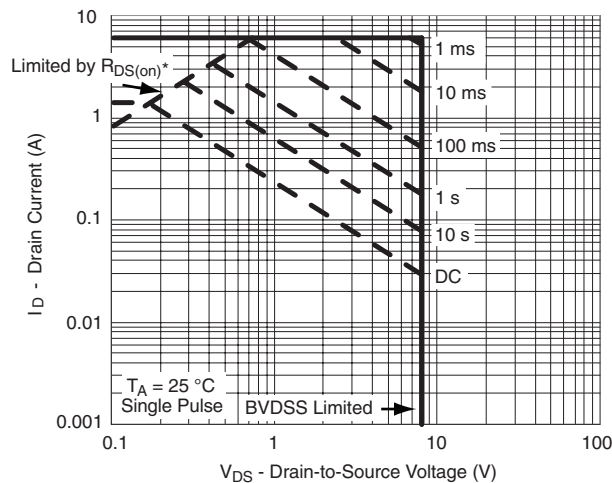
**$R_{DS(on)}$  vs  $V_{GS}$  vs Temperature**



**Threshold Voltage**



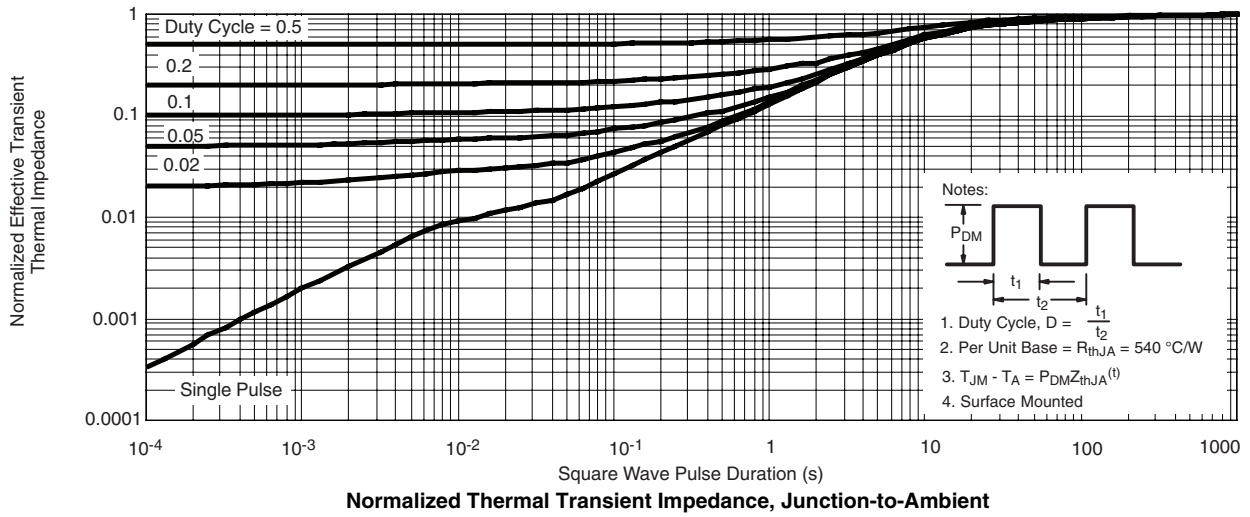
**Single Pulse Power**



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**

**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



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